

MOSFETs Silicon N-Channel MOS

# SSM6N815R

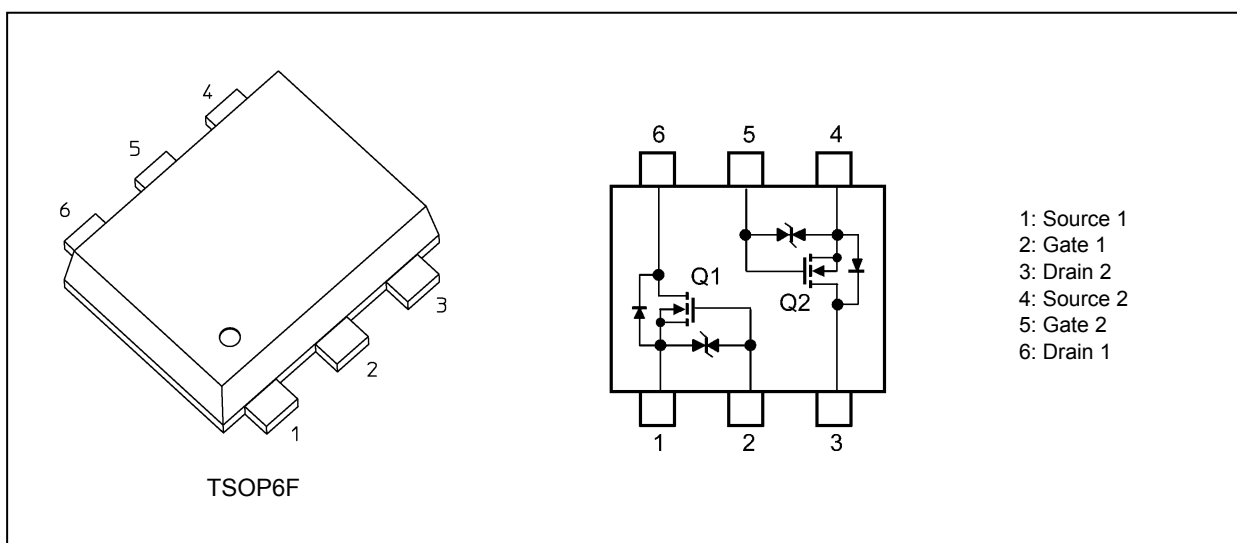
## 1. Applications

- Power Management Switches

## 2. Features

- (1) 4.0 V drive
- (2) Low drain-source on-resistance
  - :  $R_{DS(ON)} = 115 \text{ m}\Omega$  (typ.) (@ $V_{GS} = 4.0 \text{ V}$ )
  - $R_{DS(ON)} = 101 \text{ m}\Omega$  (typ.) (@ $V_{GS} = 4.5 \text{ V}$ )
  - $R_{DS(ON)} = 84 \text{ m}\Omega$  (typ.) (@ $V_{GS} = 10 \text{ V}$ )

## 3. Packaging and Pin Assignment



Start of commercial production

2017-09

### 4. Absolute Maximum Ratings (Note) (Unless otherwise specified, $T_a = 25\text{ }^\circ\text{C}$ ) (Q1, Q2 Common)

Characteristics	Symbol	Rating	Unit
Drain-source voltage	$V_{DSS}$	100	V
Gate-source voltage	$V_{GSS}$	$\pm 20$	
Drain current (DC) (Note 1)	$I_D$	2	A
Drain current (pulsed) (Note 1), (Note 2)	$I_{DP}$	4	
Power dissipation (Note 3)	$P_D$	1.4	W
Power dissipation ( $t \leq 10\text{ s}$ ) (Note 3)		1.8	
Single-pulse avalanche energy (Note 4)	$E_{AS}$	10.1	mJ
Avalanche current	$I_{AR}$	2	A
Channel temperature	$T_{ch}$	150	$^\circ\text{C}$
Storage temperature	$T_{stg}$	-55 to 150	$^\circ\text{C}$

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

Note 1: Ensure that the channel temperature does not exceed  $150\text{ }^\circ\text{C}$ .

Note 2: Pulse width (PW)  $\leq 10\text{ s}$ , duty  $\leq 1\%$

Note 3: Device mounted on an FR4 board. (PD for the entire IC)  
(FR4,  $25.4\text{ mm} \times 25.4\text{ mm} \times 1.6\text{ mm}$ , Cu pad:  $645\text{ mm}^2$ )

Note 4:  $V_{DD} = 25\text{ V}$ ,  $T_{ch} = 25\text{ }^\circ\text{C}$  (Initial state),  $L = 1\text{ mH}$ ,  $R_G = 25\ \Omega$

Note: The MOSFETs in this device are sensitive to electrostatic discharge. When handling this device, the worktables, operators, soldering irons and other objects should be protected against anti-static discharge.

Note: The channel-to-ambient thermal resistance,  $R_{th(ch-a)}$ , and the drain power dissipation,  $P_D$ , vary according to the board material, board area, board thickness and pad area. When using this device, be sure to take heat dissipation fully into account.

### 5. Electrical Characteristics

#### 5.1. Static Characteristics (Unless otherwise specified, $T_a = 25\text{ }^\circ\text{C}$ ) (Q1,Q2 Common)

Characteristics	Symbol	Test Condition	Min	Typ.	Max	Unit
Gate leakage current	$I_{GSS}$	$V_{DS} = 0\text{ V}, V_{GS} = \pm 16\text{ V}$	—	—	$\pm 10$	$\mu\text{A}$
Drain cut-off current	$I_{DSS}$	$V_{DS} = 100\text{ V}, V_{GS} = 0\text{ V}$	—	—	1	
Drain-source breakdown voltage	$V_{(BR)DSS}$	$I_D = 10\text{ mA}, V_{GS} = 0\text{ V}$	100	—	—	V
Drain-source breakdown voltage (Note 1)	$V_{(BR)DSX}$	$I_D = 10\text{ mA}, V_{GS} = -20\text{ V}$	80	—	—	
Gate threshold voltage (Note 2)	$V_{th}$	$V_{DS} = 10\text{ V}, I_D = 0.1\text{ mA}$	1.5	—	2.5	
Drain-source on-resistance (Note 3)	$R_{DS(ON)}$	$I_D = 1\text{ A}, V_{GS} = 4.0\text{ V}$	—	115	180	$\text{m}\Omega$
		$I_D = 2\text{ A}, V_{GS} = 4.5\text{ V}$	—	101	142	
		$I_D = 2\text{ A}, V_{GS} = 10\text{ V}$	—	84	103	
Forward transfer admittance (Note 3)	$ Y_{fs} $	$V_{DS} = 10\text{ V}, I_D = 2\text{ A}$	—	4.8	—	S

Note 1: If a reverse bias is applied between gate and source, this device enters  $V_{(BR)DSX}$  mode. Note that the drain-source breakdown voltage is lowered in this mode.

Note 2: Let  $V_{th}$  be the voltage applied between gate and source that causes the drain current ( $I_D$ ) to be below (0.1 mA for this device). Then, for normal switching operation,  $V_{GS(ON)}$  must be higher than  $V_{th}$ , and  $V_{GS(OFF)}$  must be lower than  $V_{th}$ . This relationship can be expressed as:  $V_{GS(OFF)} < V_{th} < V_{GS(ON)}$ .

Take this into consideration when using the device.

Note 3: Pulse measurement.

#### 5.2. Dynamic Characteristics (Unless otherwise specified, $T_a = 25\text{ }^\circ\text{C}$ ) (Q1,Q2 Common)

Characteristics	Symbol	Test Condition	Min	Typ.	Max	Unit
Input capacitance	$C_{iss}$	$V_{DS} = 15\text{ V}, V_{GS} = 0\text{ V},$ $f = 1\text{ MHz}$	—	290	—	$\text{pF}$
Reverse transfer capacitance	$C_{riss}$		—	16	—	
Output capacitance	$C_{oss}$		—	108	—	
Switching time (turn-on time)	$t_{on}$	$V_{DD} = 30\text{ V}, I_D = 1\text{ A},$ $V_{GS} = 0\text{ to }4.5\text{ V}, R_G = 50\ \Omega$ Duty $\leq 1\%$ , Input: $t_r, t_f < 5\text{ ns}$ Ground source, See Chapter 5.3	—	7.5	—	ns
Switching time (turn-off time)	$t_{off}$		—	21	—	

#### 5.3. Switching Time Test Circuit

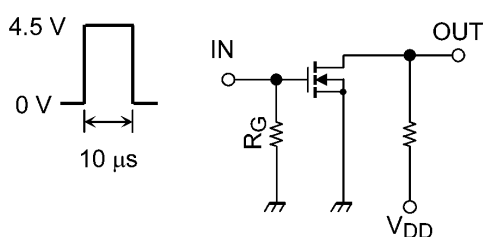


Fig. 5.3.1 Switching Time Test Circuit

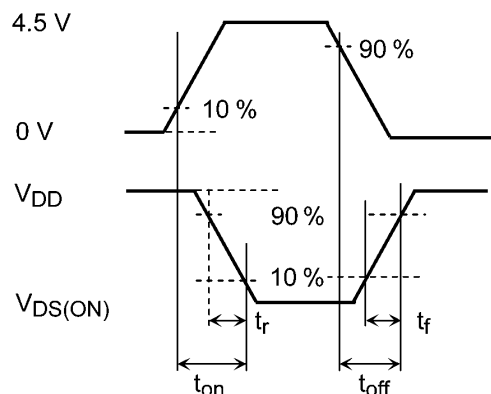


Fig. 5.3.2 Input Waveform/Output Waveform

#### 5.4. Gate Charge Characteristics (Unless otherwise specified, $T_a = 25\text{ }^\circ\text{C}$ ) (Q1,Q2 Common)

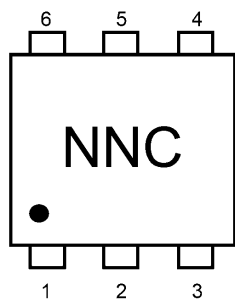
Characteristics	Symbol	Test Condition	Min	Typ.	Max	Unit
Total gate charge (gate-source plus gate-drain)	$Q_g$	$V_{DD} = 50\text{ V}, I_D = 2\text{ A},$ $V_{GS} = 4.5\text{ V}$	—	3.1	—	nC
Gate-source charge 1	$Q_{gs1}$		—	1.1	—	
Gate-drain charge	$Q_{gd}$		—	1.5	—	

## 5.5. Source-Drain Characteristics (Unless otherwise specified, $T_a = 25\text{ }^\circ\text{C}$ ) (Q1,Q2 Common)

Characteristics	Symbol	Test Condition	Min	Typ.	Max	Unit
Diode forward voltage (Note 1)	$V_{DSF}$	$I_D = -2\text{ A}, V_{GS} = 0\text{ V}$	—	-0.9	-1.5	V

Note 1: Pulse measurement.

## 6. Marking



### 7. Characteristics Curves (Q1,Q2 Common) (Note)

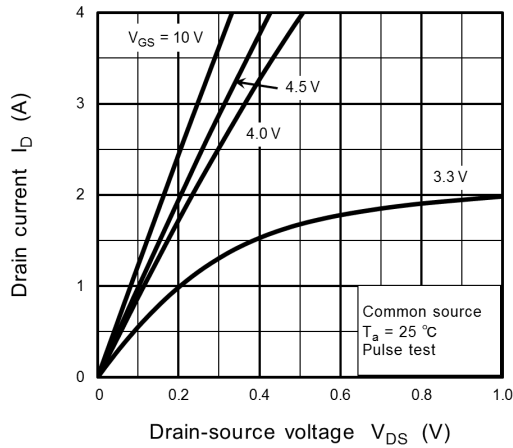


Fig. 7.1  $I_D - V_{DS}$

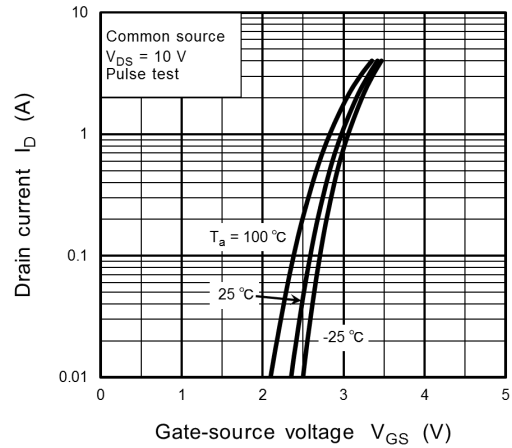


Fig. 7.2  $I_D - V_{GS}$

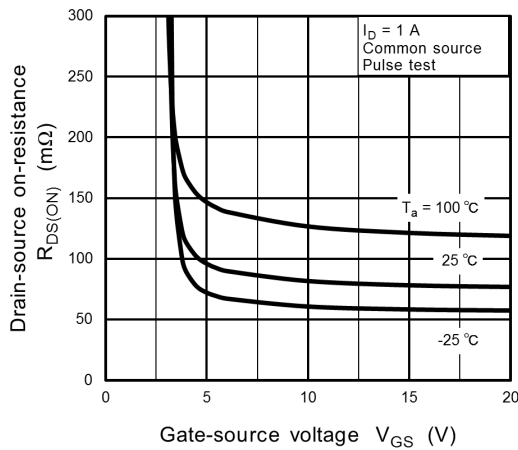


Fig. 7.3  $R_{DS(ON)} - V_{GS}$

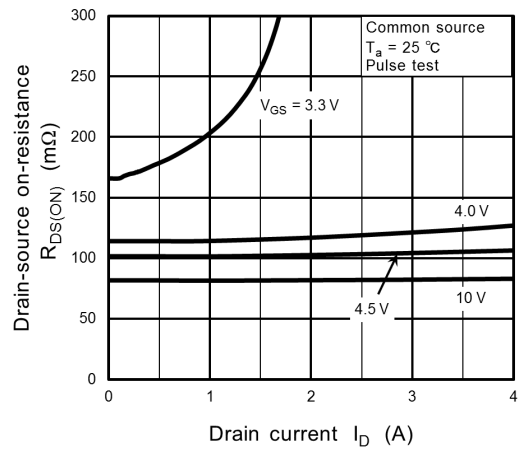


Fig. 7.4  $R_{DS(ON)} - I_D$

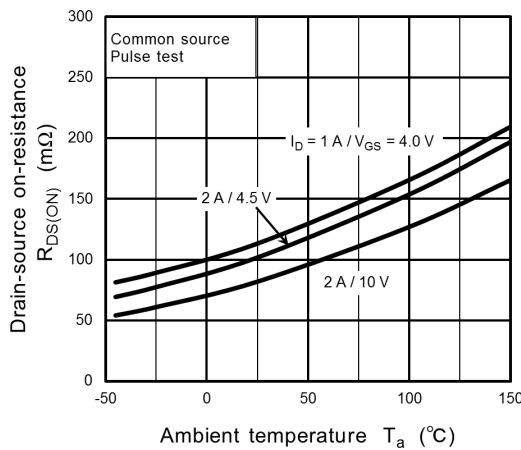


Fig. 7.5  $R_{DS(ON)} - T_a$

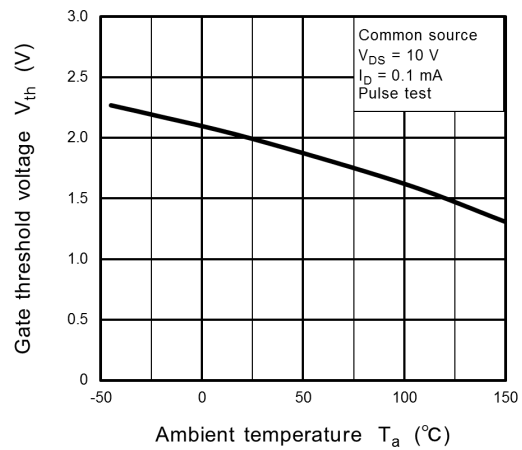
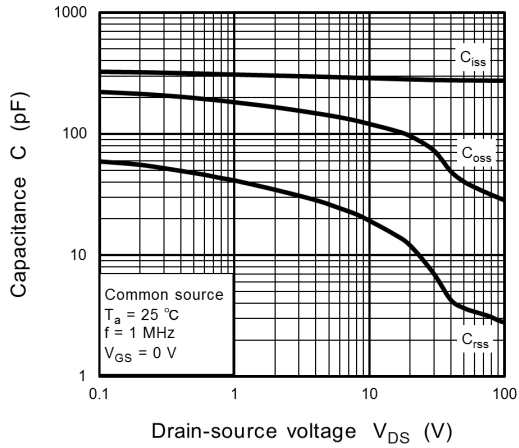
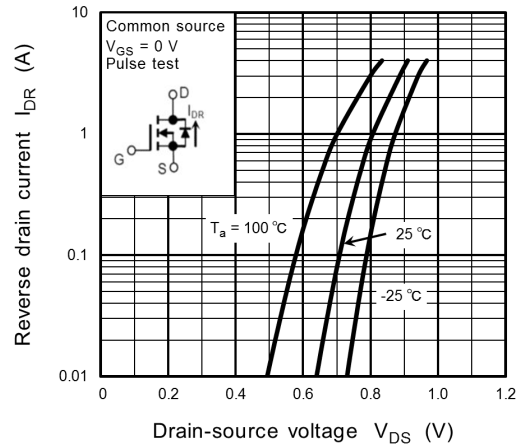


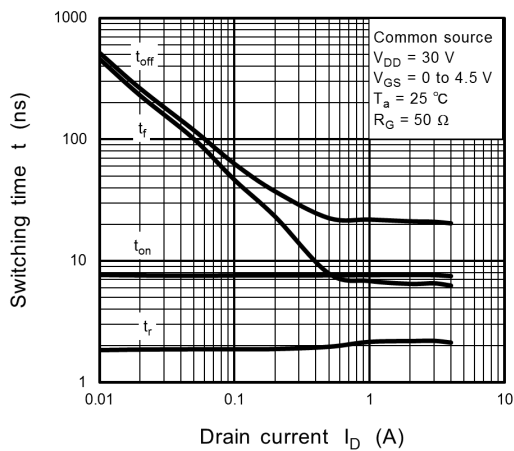
Fig. 7.6  $V_{th} - T_a$



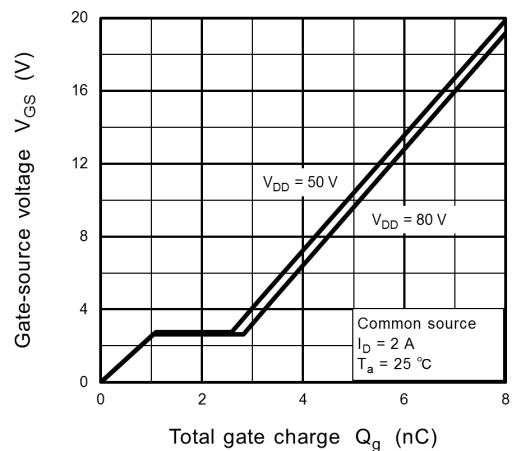
**Fig. 7.7 C -  $V_{DS}$**



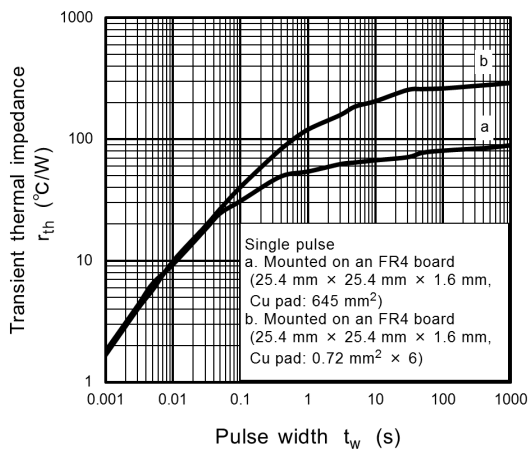
**Fig. 7.8  $I_{DR}$  -  $V_{DS}$**



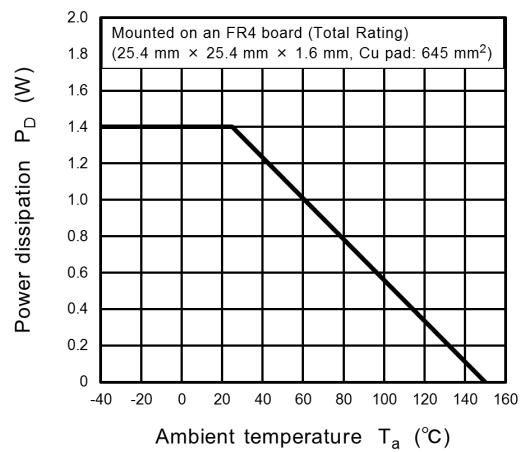
**Fig. 7.9 t -  $I_D$**



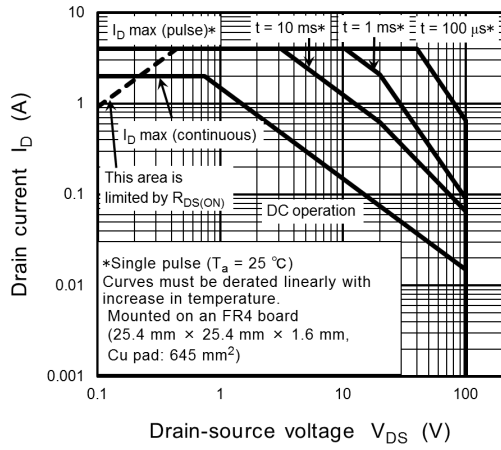
**Fig. 7.10 Dynamic Input Characteristics**



**Fig. 7.11  $r_{th}$  -  $t_w$**



**Fig. 7.12  $P_D$  -  $T_a$**



**Fig. 7.13 Safe Operating Area**

Note: The above characteristics curves are presented for reference only and not guaranteed by production test, unless otherwise noted.

## Package Dimensions

Unit: mm



Weight: 0.016 g (typ.)

Package Name(s)
Nickname: TSOP6F



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